

CDx4HC112、CDx4HCT112 具有设置与复位功能的 双路负边沿触发式 J-K 触发器

1 特性

- 时钟输入迟滞，改进了抗噪性能并增加了输入上升和下降时间
- 异步设置与复位
- 互补输出
- 缓冲输入
- $V_{CC} = 5V$ 、 $C_L = 15pF$ 且 $T_A = 25^\circ C$ 时的 f_{MAX} 典型值为 60MHz
- 扇出 (在温度范围内)
 - 标准输出：10 个 LSTTL 负载
 - 总线驱动器输出：15 个 LSTTL 负载
- 宽工作温度范围： $-55^\circ C$ 至 $+125^\circ C$
- 平衡的传播延迟及转换时间
- 与 LSTTL 逻辑 IC 相比，功耗显著降低
- HC 类型
 - 工作电压为 2V 至 6V
 - 高抗噪性：当 $V_{CC} = 5V$ 时， $N_{IL} = 30\%$ ， $N_{IH} = V_{CC}$ 的 30%
- HCT 类型
 - 工作电压为 4.5V 至 5.5V
 - 直接 LSTTL 输入逻辑兼容性， $V_{IL} = 0.8V$ (最大值)， $V_{IH} = 2V$ (最小值)
 - CMOS 输入兼容性，当电压为 V_{OL} 、 V_{OH} 时， $I_I \leq 1\mu A$

2 说明

'HC112 和 'HCT112 采用硅栅 CMOS 技术，可实现相当于 LSTTL 器件的运行速度；具有标准 CMOS 集成电路的低功耗特性，并能够驱动 10 个 LSTTL 负载。

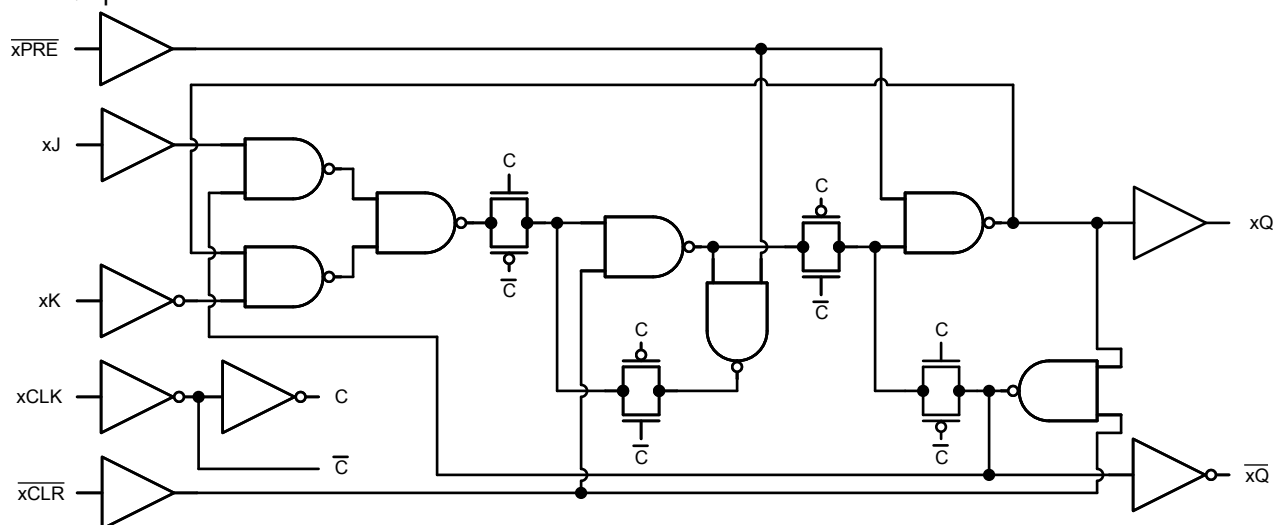
这些触发器具有独立的 J、K、 $\overline{PRE}$ 、 $\overline{CLR}$ 和时钟输入以及 Q 和 $\overline{Q}$ 输出，会在时钟脉冲发生负向转换时更改状态。 $\overline{PRE}$ 和 $\overline{CLR}$ 均由低电平输入异步实现。

该 HCT 系列逻辑器件与标准 LS 系列逻辑器件功能和引脚兼容。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)
CD54HC112F3A	CDIP (16)	24.38mm × 6.92mm
CD74HC112M96	SOIC (16)	9.90mm × 3.90mm
CD74HC112E	PDIP (16)	19.31mm × 6.35mm
CD74HCT112E	PDIP (16)	19.31mm × 6.35mm
CD74HC112NSR	SO (16)	6.20mm × 5.30mm
CD74HC112PW	TSSOP (16)	5.00mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



功能图



Table of Contents

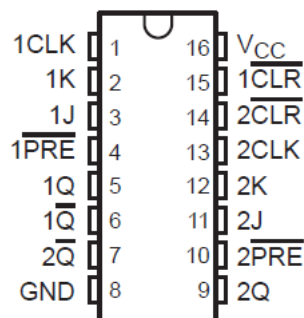
1 特性	1	7.2 Functional Block Diagram.....	10
2 说明	1	7.3 Device Functional Modes.....	10
3 Revision History	2	8 Power Supply Recommendations	11
4 Pin Configuration and Functions	3	9 Layout	11
5 Specifications	4	9.1 Layout Guidelines.....	11
5.1 Absolute Maximum Ratings.....	4	10 Device and Documentation Support	12
5.2 Recommended Operating Conditions.....	4	10.1 接收文档更新通知.....	12
5.3 Thermal Information.....	4	10.2 支持资源.....	12
5.4 Electrical Characteristics.....	5	10.3 Trademarks.....	12
5.5 Prerequisite for Switching Characteristics.....	6	10.4 Electrostatic Discharge Caution.....	12
5.6 Switching Characteristics.....	7	10.5 术语表.....	12
6 Parameter Measurement Information	8	11 Mechanical, Packaging, and Orderable Information	12
7 Detailed Description	10		
7.1 Overview.....	10		

3 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision I (January 2022) to Revision J (October 2022)	Page
• Increased R _{θJA} for packages: D (73 to 117.2); N (67 to 69.3); NS (64 to 88.4); PW (108 to 137.5).....	4
Changes from Revision H (October 2003) to Revision I (January 2022)	Page
• 更新了整个文档中的编号、格式、表格、图和交叉参考，以反映现代数据表标准.....	1
• Updated pin names to match current standards. $\overline{CP}$ is now CLK; $\overline{S}$ is now $\overline{PRE}$; $1R$ is now $1\overline{CLR}$; $2R$ is now $2\overline{CLR}$; $2\overline{CP}$ is now 2CLK; $2\overline{S}$ is now $2\overline{PRE}$	3

4 Pin Configuration and Functions



J, N, D, NS, or PW package
16-Pin CDIP, PDIP, SOIC, SO, TSSOP
Top View

5 Specifications

5.1 Absolute Maximum Ratings

(1)			MIN	MAX	UNIT
V_{CC}	Supply voltage		- 0.5	7	V
I_{IK}	Input diode current	For $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$		± 20	mA
I_O	Drain current, per output	For $-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$		± 25	mA
I_{OK}	Output diode current	For $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$		± 20	mA
I_O	Output source or sink current per output pin	For $V_O > -0.5\text{ V}$ or $V_O < V_{CC} + 0.5\text{ V}$		± 25	mA
I_{CC}	Continuous current through V_{CC} or GND			± 50	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature range		- 65	150	°C
	Lead temperature (Soldering 10s)			300	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 Recommended Operating Conditions

			MIN	MAX	UNIT
V_{CC}	Supply voltage range	HC types	2	6	V
		HCT types	4.5	5.5	
V_I, V_O	Input or output voltage		0	V_{CC}	V
t_r, t_f	Input rise and fall time	2 V		1	ms
		4.5 V		1	
		6 V		1	
T_A	Temperature range		- 55	125	°C

5.3 Thermal Information

THERMAL METRIC		D (SOIC)	N (PDIP)	NS (SO)	PW (TSSOP)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾	117.2	69.3	88.4	137.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	77.2	61.8	46	75.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	75.6	49.3	50.6	82.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	38.1	34.6	13	25.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	75.3	49	50.2	81.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.4 Electrical Characteristics

PARAMETER		TEST CONDITIONS ⁽²⁾	V _{CC} (V)	25°C			– 40°C to 85°C		– 55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
V _{IH}	High level input voltage		2	1.5			1.5		1.5		V
			4.5	3.15			3.15		3.15		
			6	4.2			4.2		4.2		
V _{IL}	Low level input voltage		2	0.5			0.5		0.5		V
			4.5	1.35			1.35		1.35		
			6	1.8			1.8		1.8		
V _{OH}	High level output voltage	I _{OH} = – 20 μA	2	1.9			1.9		1.9		V
			4.5	4.4			4.4		4.4		
			6	5.9			5.9		5.9		
	High level output voltage	I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		
		I _{OH} = – 5.2 mA	6	5.48			5.34		5.2		
V _{OL}	Low level output voltage	I _{OL} = 20 μA	2	0.1			0.1		0.1		V
			4.5	0.1			0.1		0.1		
			6	0.1			0.1		0.1		
	Low level output voltage	I _{OL} = 4 mA	4.5	0.26			0.33		0.4		
		I _{OL} = 5.2 mA	6	0.26			0.33		0.4		
I _I	Input leakage current	V _{CC} or GND	6	±0.1			±1		±1		μA
I _{CC}	Supply current	V _{CC} or GND	6	4			40		80		μA
HCT TYPES											
V _{IH}	High level input voltage		4.5 to 5.5	2			2		2		V
V _{IL}	Low level input voltage		4.5 to 5.5	0.8			0.8		0.8		V
V _{OH}	High level output voltage	I _{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
	High level output voltage	I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		
V _{OL}	Low level output voltage	I _{OL} = 20 μA	4.5	0.1			0.1		0.1		V
	Low level output voltage	I _{OL} = 4 mA	4.5	0.26			0.33		0.4		
I _I	Input leakage current	V _{CC} and GND	5.5	±0.1			±1		±1		μA
I _{CC}	Supply current	V _{CC} and GND	5.5	4			40		80		μA
Δ I _{CC} (1)	Additional supply current per input pin	1PRE, 2PRE inputs held at V _{CC} -2.1	4.5 to 5.5	100 180			225		245		μA
		1K, 2K inputs held at V _{CC} -2.1	4.5 to 5.5	100 216			270		294		μA
		1CLR, 2CLR inputs held at V _{CC} -2.1	4.5 to 5.5	100 234			292.5		318.5		μA
		1J, 2J, 1CLK, 2CLK inputs held at V _{CC} -2.1	4.5 to 5.5	100 360			450		490		μA

(1) For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

(2) $V_I = V_{IH}$ or V_{IL} , unless otherwise noted.

5.5 Prerequisite for Switching Characteristics

PARAMETER		V _{CC} (V)	25°C			– 40°C to 85°C		– 55°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES										
t _W	Pulse width CLK	2	80			100		120		ns
		4.5	16			20		24		
		6	14			17		20		
t _W	Pulse width $\overline{\text{CLR}}$, PRE	2	80			100		120		ns
		4.5	16			20		24		
		6	14			17		20		
t _{SU}	Setup time J, K, to CLK	2	80			100		120		ns
		4.5	16			20		24		
		6	14			17		20		
t _H	Hold time J, K, to CLK	2	0			0		0		ns
		4.5	0			0		0		
		6	0			0		0		
t _{REM}	Removal time $\overline{\text{CLR}}$ to CLK, $\overline{\text{PRE}}$ to CLK	2	80			100		120		ns
		4.5	16			20		24		
		6	14			17		20		
f _{MAX}	CLK frequency	2	6			5		4		MHz
		4.5	30			25		20		
		6	35			29		23		
HCT TYPES										
t _{SU}	Pulse width CLK	4.5	16			20		24		ns
t _W	Pulse width $\overline{\text{CLR}}$, PRE	4.5	18			23		27		ns
t _H	Setup time J, K, to CLK	4.5	16			20		24		ns
t _{REM}	Hold time J, K, to CLK	4.5	3			3		3		ns
t _W	Removal time $\overline{\text{CLR}}$ to CLK, PRE to CLK	4.5	20			25		30		ns
f _{MAX}	CLK frequency	4.5	30			25		20		MHz

5.6 Switching Characteristics

$t_r, t_f = 6 \text{ ns}$

PARAMETER		V _{CC} (V)	25°C			– 40°C to 85°C		– 55°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES										
t _{PLH} , t _{PHL}	Propagation delay, CLK to Q, $\bar{Q}$	2			175		220		265	ns
		4.5		14 ⁽³⁾	35		44		53	
		6			30		37		45	
t _{PLH} , t _{PHL}	Propagation delay, PRE to Q, $\bar{Q}$	2			155		195		235	ns
		4.5		13 ⁽³⁾	31		39		47	
		6			26		33		40	
t _{PLH} , t _{PHL}	Propagation delay, CLR to Q, $\bar{Q}$	2			180		225		270	ns
		4.5		15 ⁽³⁾	36		45		54	
		6			31		38		46	
t _{TLH} , t _{THL}	Output transition time	2			75		95		110	ns
		4.5			15		19		22	
		6			13		16		19	
C _I	Input capacitance				10		10		10	pF
f _{MAX}	CLK frequency	5		60 ⁽³⁾						MHz
C _{PD}	Power dissipation capacitance ^{(1) (2)}	5		12 ⁽⁴⁾						pF
HCT TYPES										
t _{PLH} , t _{PHL}	Propagation delay, CLK to Q, $\bar{Q}$	4.5		14 ⁽³⁾	35		44		53	ns
t _{PLH} , t _{PHL}	Propagation delay, PRE to Q, $\bar{Q}$	4.5		13 ⁽³⁾	32		40		48	ns
t _{PLH} , t _{PHL}	Propagation delay, $\bar{C}$ LR to Q, $\bar{Q}$	4.5		14 ⁽³⁾	37		46		56	ns
t _{TLH} , t _{THL}	Output transition time	4.5			15		19		22	ns
C _I	Input capacitance				10		10		10	pF
f _{MAX}	CLK frequency	5		60 ⁽³⁾						MHz
C _{PD}	Power dissipation capacitance ^{(1) (2)}	5		20 ⁽⁴⁾						pF

(1) C_{PD} is used to determine the dynamic power consumption, per flip-flop.

(2) $P_D = C_{PD} V_{CC}^2 f_i + \sum C_L f_o$ where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, V_{CC} = supply voltage.

(3) $C_L = 15 \text{ pF}$ and $V_{CC} = 5 \text{ V}$.

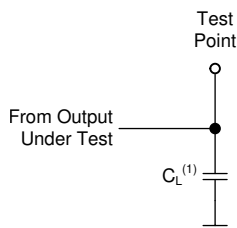
(4) $V_{CC} = 5 \text{ V}$.

6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $\text{PRR} \leq 1 \text{ MHz}$, $Z_O = 50 \, \Omega$, $t_f < 6 \text{ ns}$.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

图 6-1. Load Circuit for Push-Pull Outputs

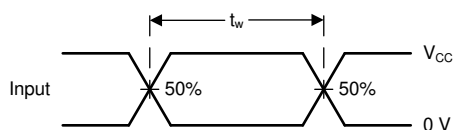


图 6-2. Voltage Waveforms, Standard CMOS Inputs
Pulse Duration

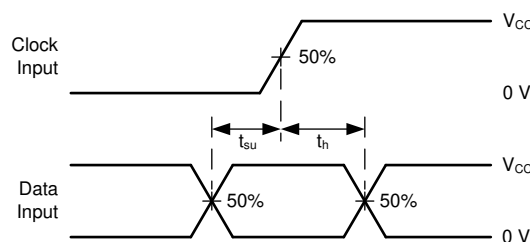
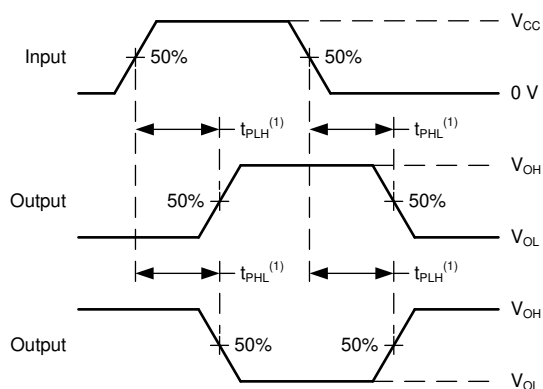
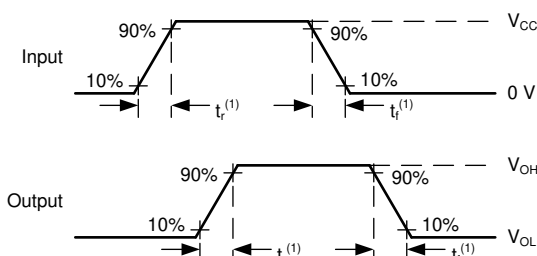


图 6-3. Voltage Waveforms, Standard CMOS Inputs
Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

图 6-4. Voltage Waveforms, Propagation Delays for
Standard CMOS Inputs



(1) The greater between t_r and t_f is the same as t_t .

图 6-5. Voltage Waveforms, Input and Output
Transition Times for Standard CMOS Inputs



图 6-6. Voltage Waveforms, TTL-Compatible CMOS Inputs Pulse Duration

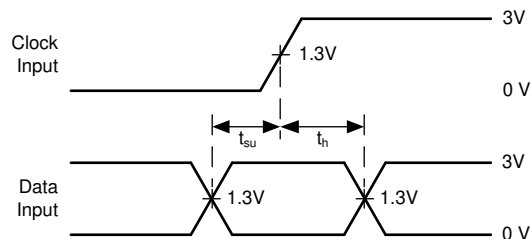
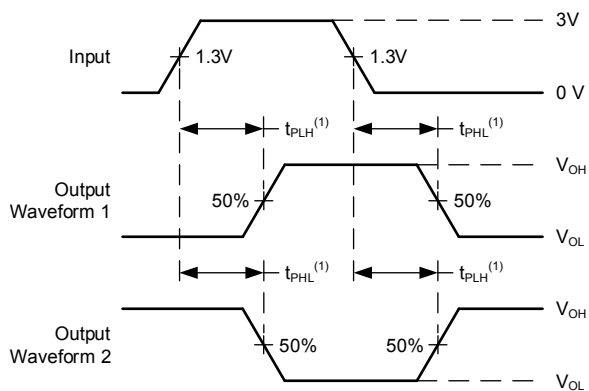


图 6-7. Voltage Waveforms, TTL-Compatible CMOS Inputs Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

图 6-8. Voltage Waveforms, Propagation Delays for TTL-Compatible Inputs

7 Detailed Description

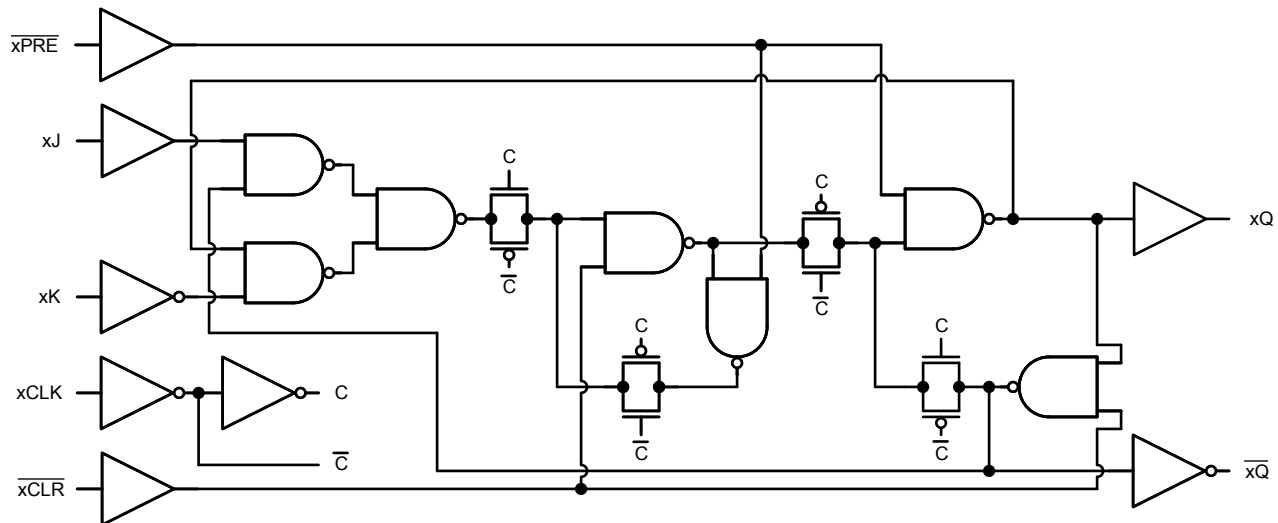
7.1 Overview

The 'HC112 and 'HCT112 utilize silicon-gate CMOS technology to achieve operating speeds equivalent to LSTTL parts. They exhibit the low power consumption of standard CMOS integrated circuits, together with the ability to drive 10 LSTTL loads.

These flip-flops have independent J, K, $\overline{\text{PRE}}$, $\overline{\text{CLR}}$, and Clock inputs and Q and $\overline{\text{Q}}$ outputs. They change state on the negative-going transition of the clock pulse. PRE and CLR are accomplished asynchronously by low-level inputs.

The HCT logic family is functionally and pin-compatible with the standard LS logic family.

7.2 Functional Block Diagram



7.3 Device Functional Modes

表 7-1. Truth Table⁽¹⁾

INPUTS					OUTPUTS	
PRE	CLR	CLK	J	K	Q	Q̄
L	H	X	X	X	H	L
H	L	X	X	X	L	H
L	L	X	X	X	H ⁽²⁾	H ⁽²⁾
H	H	–	L	L	No Change	
H	H	–	H	L	H	L
H	H	–	L	H	L	H
H	H	–	H	H	Toggle	
H	H	H	X	X	No Change	

(1) H = high level (steady state), L = low level (steady state), X = don't care, ↓ = high-to-low transition

(2) Output states unpredictable if both S and R go high simultaneously after both being low at the same time.

8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
5962-8970201EA	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8970201EA CD54HCT112F3A
CD54HC112F3A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	8408801EA CD54HC112F3A
CD54HC112F3A.A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	8408801EA CD54HC112F3A
CD54HCT112F3A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8970201EA CD54HCT112F3A
CD54HCT112F3A.A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8970201EA CD54HCT112F3A
CD74HC112E	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC112E
CD74HC112E.A	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC112E
CD74HC112M96	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC112M
CD74HC112M96.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC112M
CD74HC112MT	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-55 to 125	HC112M
CD74HC112NSR	Active	Production	SOP (NS) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC112M
CD74HC112NSR.A	Active	Production	SOP (NS) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC112M
CD74HC112PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-55 to 125	HJ112
CD74HC112PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HJ112
CD74HC112PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HJ112
CD74HCT112E	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT112E
CD74HCT112E.A	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT112E

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF CD54HC112, CD54HCT112, CD74HC112, CD74HCT112 :

- Catalog : [CD74HC112](#), [CD74HCT112](#)
- Military : [CD54HC112](#), [CD54HCT112](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC112M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HC112NSR	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
CD74HC112PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD74HC112PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC112M96	SOIC	D	16	2500	340.5	336.1	32.0
CD74HC112NSR	SOP	NS	16	2000	353.0	353.0	32.0
CD74HC112PWR	TSSOP	PW	16	2000	353.0	353.0	32.0
CD74HC112PWR	TSSOP	PW	16	2000	353.0	353.0	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
CD74HC112E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC112E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC112E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC112E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT112E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT112E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT112E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT112E.A	N	PDIP	16	25	506	13.97	11230	4.32

J (R-GDIP-T**)

14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE

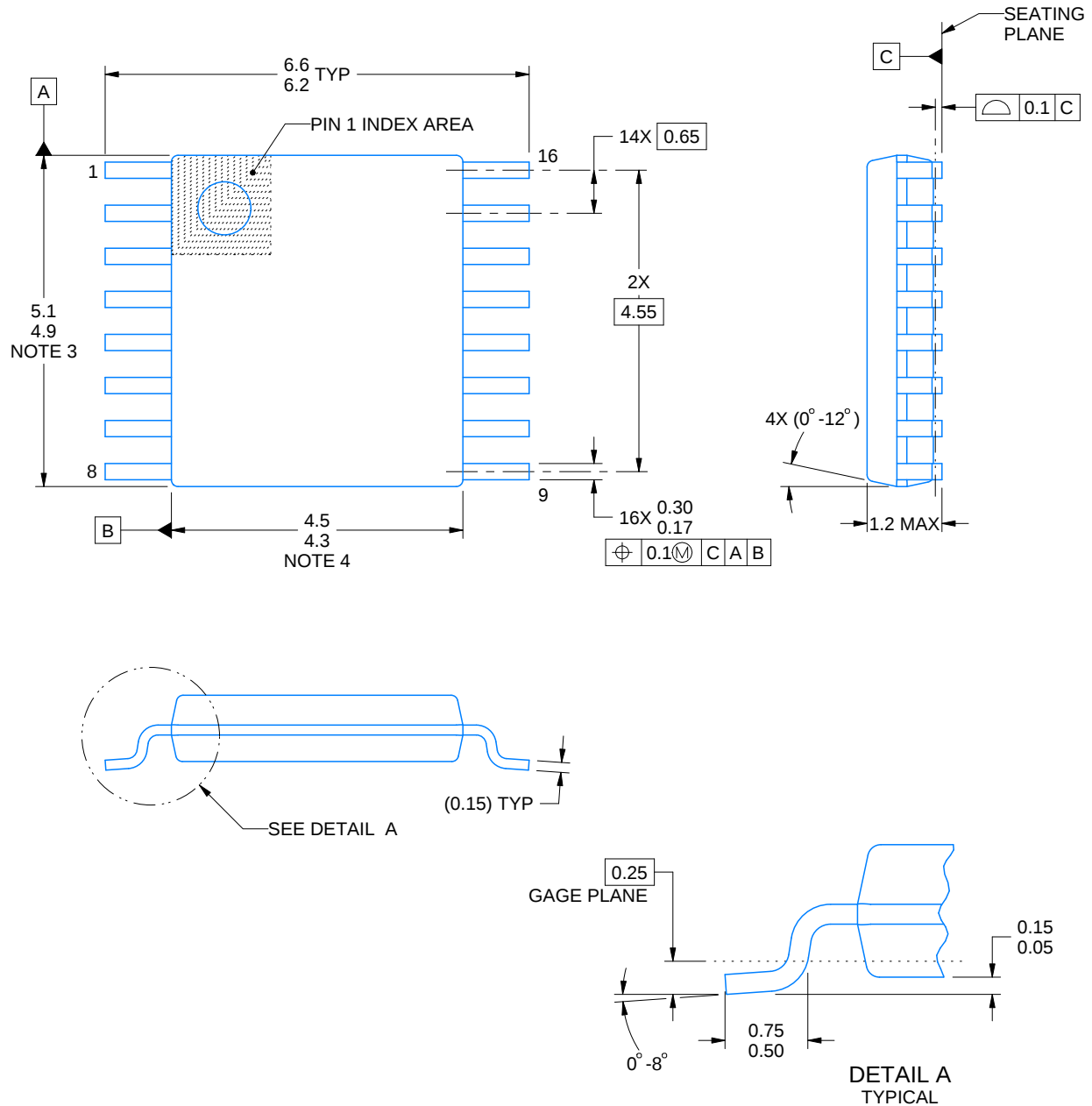
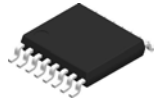


PINS ** DIM	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



4040083/F 03/03

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. This package is hermetically sealed with a ceramic lid using glass frit.
 - D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
 - E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.



4220204/B 12/2023

NOTES:

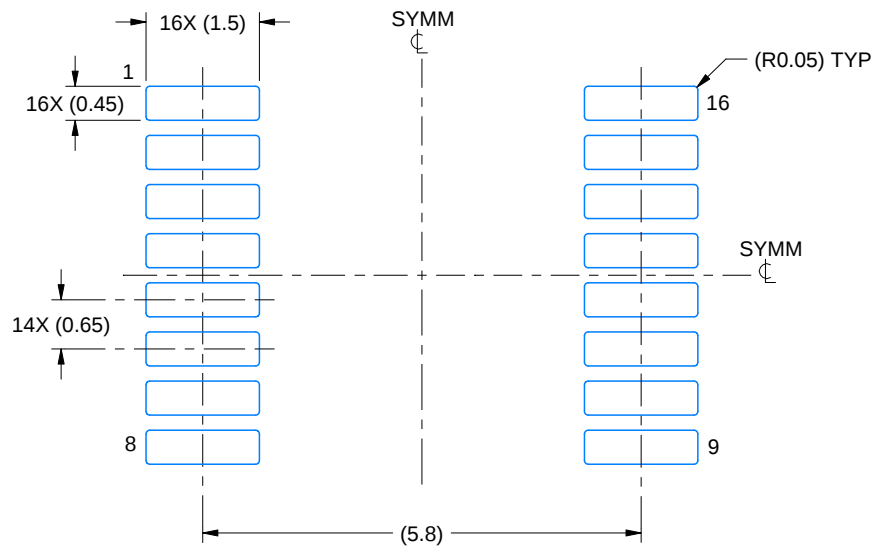
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

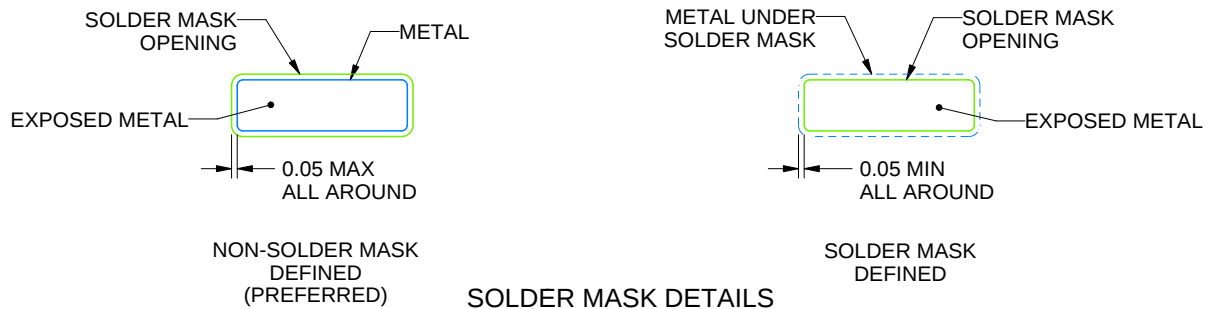
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

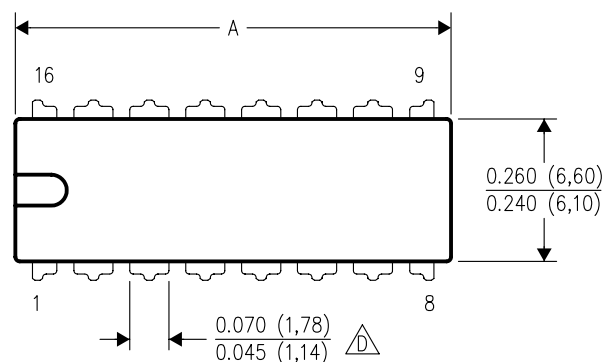
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

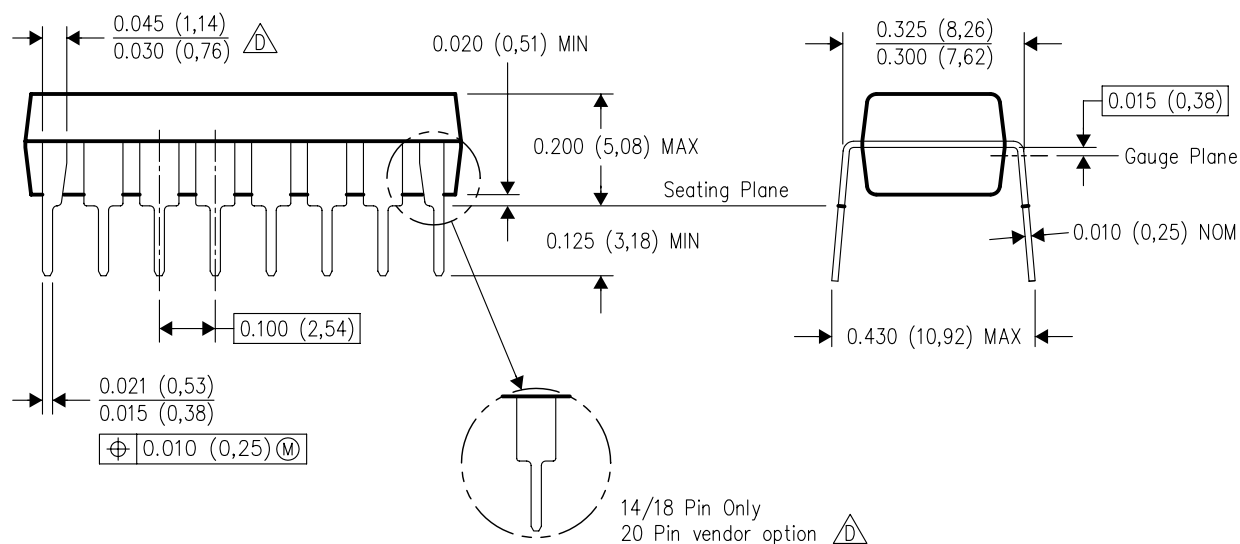
N (R-PDIP-T**)

16 PINS SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



PINS **	14	16	18	20
DIM				
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS-001 VARIATION	AA	BB	AC	AD



4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - D. The 20 pin end lead shoulder width is a vendor option, either half or full width.



PACKAGE OUTLINE

NS0016A

SOP - 2.00 mm max height

SOP



4220735/A 12/2021

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL
 SCALE:7X

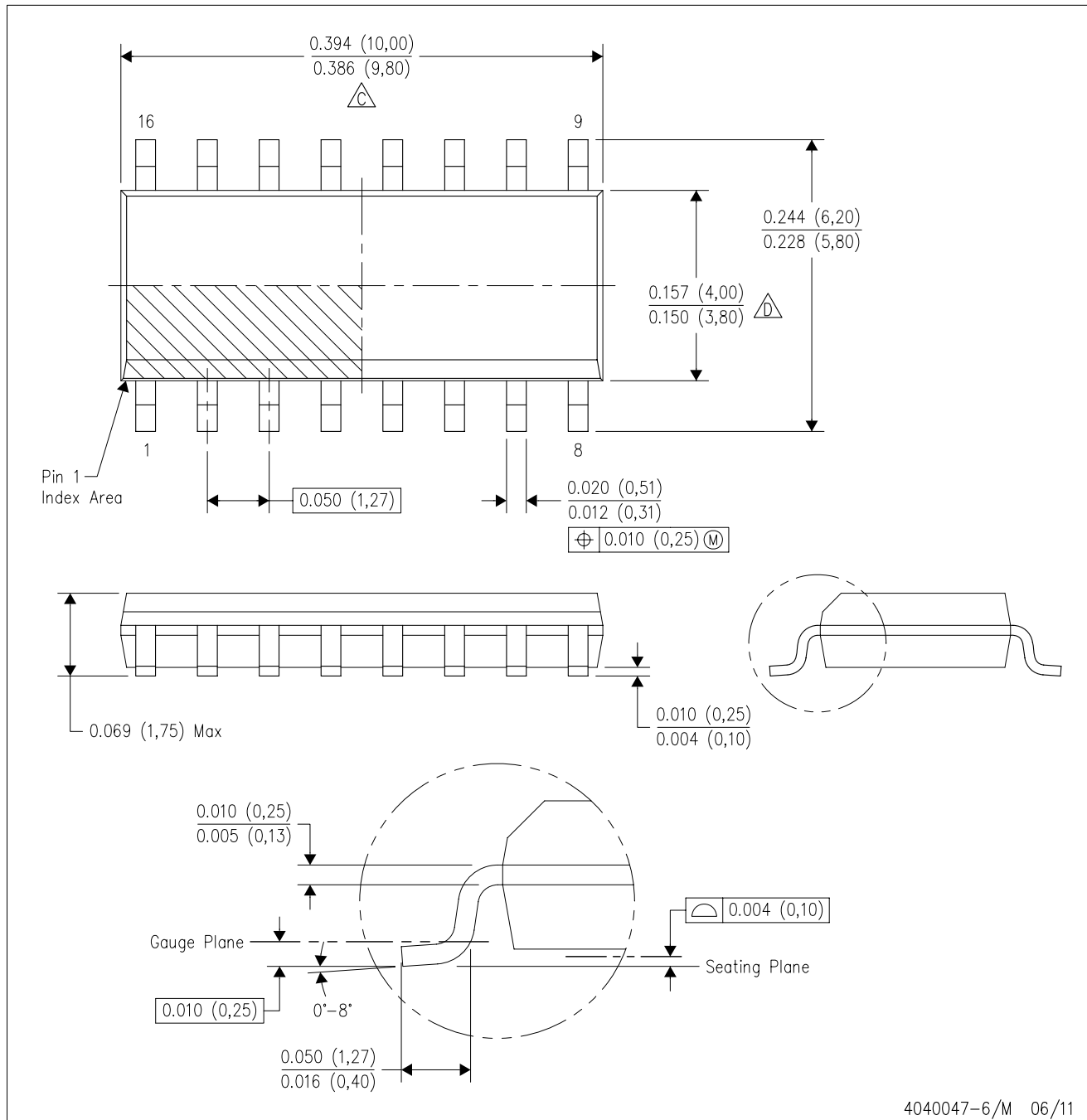
4220735/A 12/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.

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